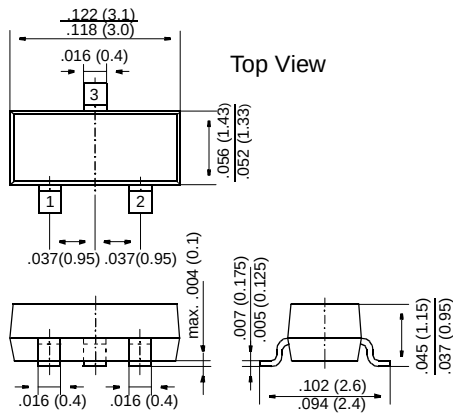


BC807, BC808

Small Signal Transistors (PNP)

SOT-23



Dimensions in inches and (millimeters)

Pin configuration

1 = Base, 2 = Emitter, 3 = Collector.

FEATURES

- ◆ PNP Silicon Epitaxial Planar Transistors for switching, AF driver and amplifier applications.
- ◆ Especially suited for automatic insertion in thick- and thin-film circuits.
- ◆ These transistors are subdivided into three groups -16, -25 and -40 according to their current gain.
- ◆ As complementary types, the NPN transistors BC817 and BC818 are recommended.



MECHANICAL DATA

Case: SOT-23 Plastic Package

Weight: approx. 0.008 g

Marking code

Type	Marking
BC807-16	5A
-25	5B
-40	5C
BC808-16	5E
-25	5F
-40	5G

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Collector-Emitter Voltage	BC807 $-V_{CES}$	50	V
	BC808 $-V_{CES}$	30	V
Collector-Emitter Voltage	BC807 $-V_{CEO}$	45	V
	BC808 $-V_{CEO}$	25	V
Emitter-Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	500	mA
Peak Collector Current	$-I_{CM}$	1000	mA
Peak Base Current	$-I_{BM}$	200	mA
Peak Emitter Current	I_{EM}	1000	mA
Power Dissipation at $T_{SB} = 50\text{ °C}$	P_{tot}	310 ¹⁾	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	-65 to +150	°C

¹⁾ Device on fiberglass substrate, see layout

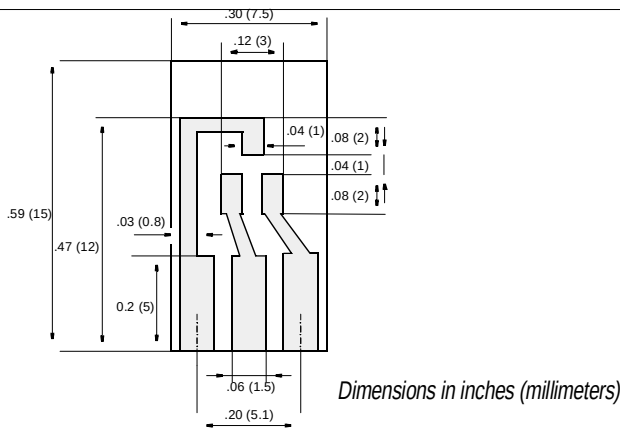
BC807, BC808

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 1 \text{ V}$, $-I_C = 100 \text{ mA}$					
Current Gain Group-16	h_{FE}	100	—	250	—
-25	h_{FE}	160	—	400	—
-40	h_{FE}	250	—	600	—
at $-V_{CE} = 1 \text{ V}$, $-I_C = 300 \text{ mA}$	h_{FE}	60	—	—	—
-16	h_{FE}	100	—	—	—
-25	h_{FE}	170	—	—	—
-40	h_{FE}	170	—	—	—
Thermal Resistance Junction Substrate Backside	R_{thSB}	—	—	320 ¹⁾	K/W
Thermal Resistance Junction to Ambient Air	R_{thJA}	—	—	450 ¹⁾	K/W
Collector Saturation Voltage at $-I_C = 500 \text{ mA}$, $-I_B = 50 \text{ mA}$	$-V_{CEsat}$	—	—	0.7	V
Base-Emitter Voltage at $-V_{CE} = 1 \text{ V}$, $-I_C = 300 \text{ mA}$	$-V_{BE}$	—	—	1.2	V
Collector-Emitter Cutoff Current at $-V_{CE} = 45 \text{ V}$ at $-V_{CE} = 25 \text{ V}$ at $-V_{CE} = 25 \text{ V}$, $T_j = 150 \text{ °C}$	$-I_{CES}$ $-I_{CES}$ $-I_{CES}$	— — —	— — —	100 100 5	nA nA μA
Emitter-Base Cutoff Current at $-V_{EB} = 4 \text{ V}$	$-I_{EBO}$	—	—	100	nA
Gain-Bandwidth Product at $-V_{CE} = 5 \text{ V}$, $-I_C = 10 \text{ mA}$, $f = 50 \text{ MHz}$	f_T	—	100	—	MHz
Collector-Base Capacitance at $-V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{CBO}		12		pF

¹⁾ Device on fiberglass substrate, see layout



Layout for R_{thJA} test

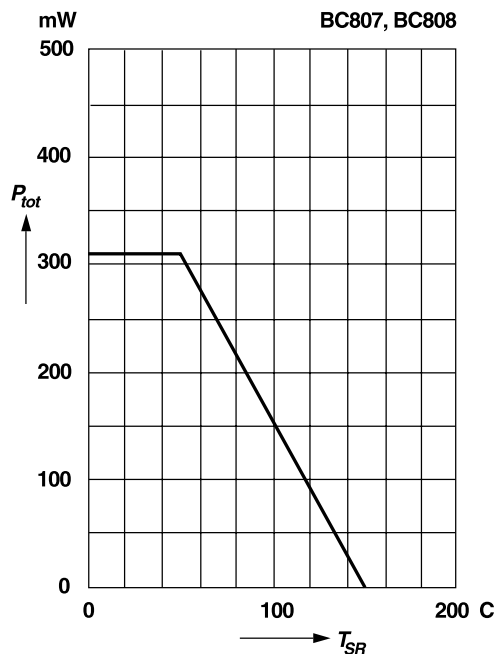
Thickness: Fiberglass 0.059 in (1.5 mm)

Copper leads 0.012 in (0.3 mm)

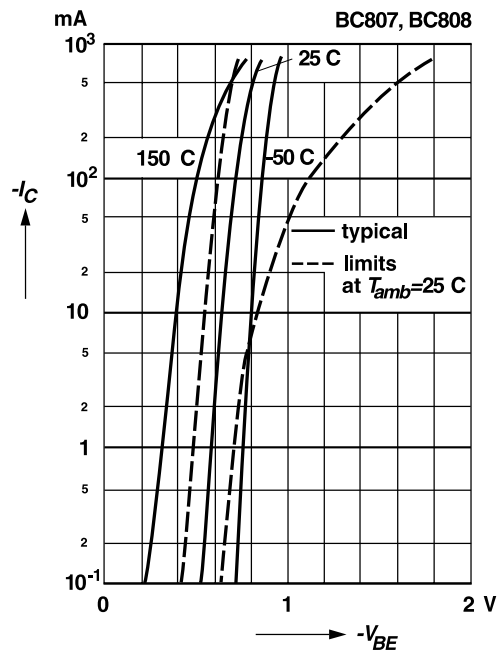
RATINGS AND CHARACTERISTIC CURVES BC807, BC808

**Admissible power dissipation
versus temperature of substrate backside**

Device on fiberglass substrate, see layout

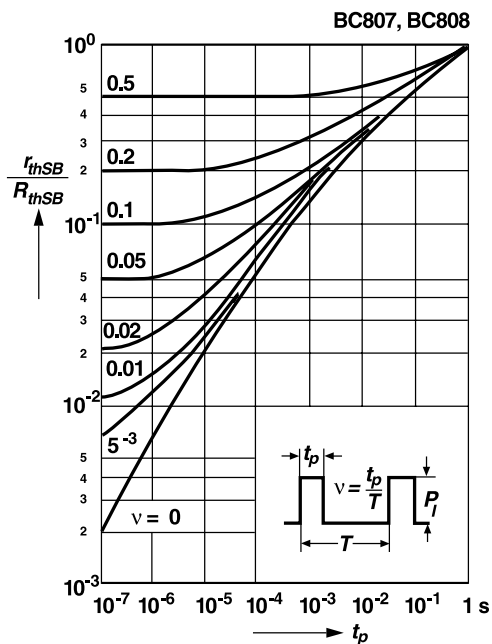


**Collector current
versus base-emitter voltage**

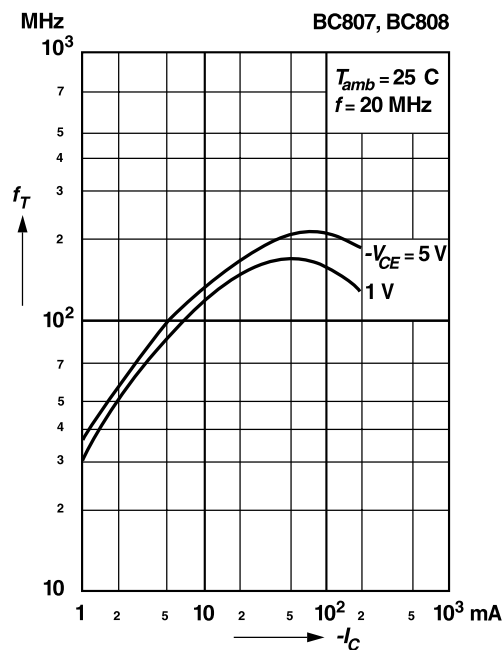


**Pulse thermal resistance
versus pulse duration (normalized)**

Device on fiberglass substrate, see layout

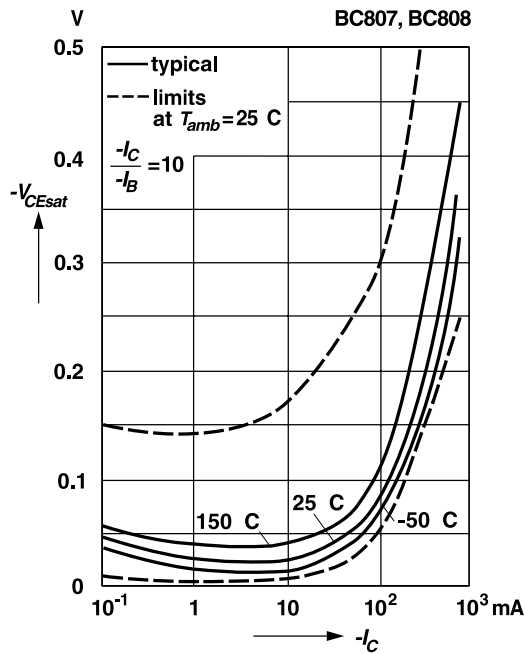


**Gain-bandwidth product
versus collector current**

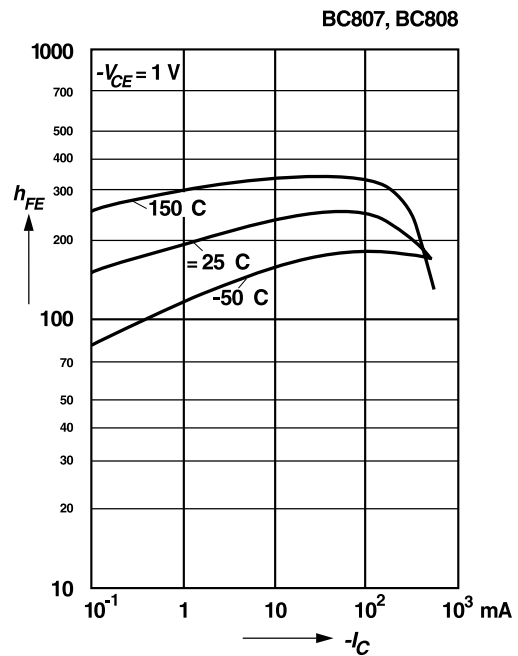


RATINGS AND CHARACTERISTIC CURVES BC807, BC808

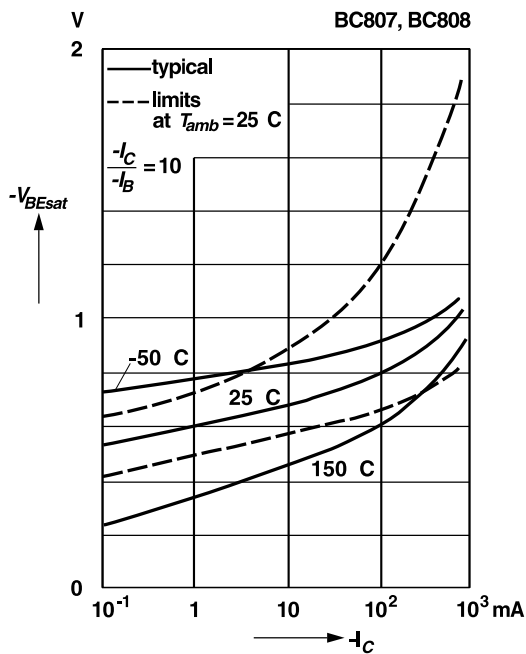
Collector saturation voltage
versus collector current



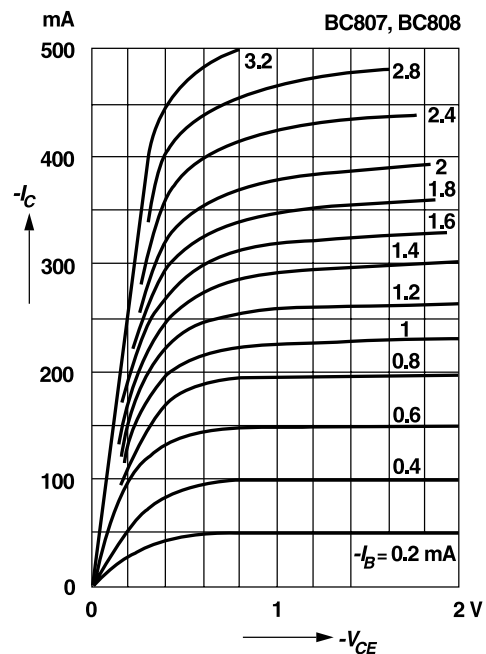
DC current gain
versus collector current



Base saturation voltage
versus collector current

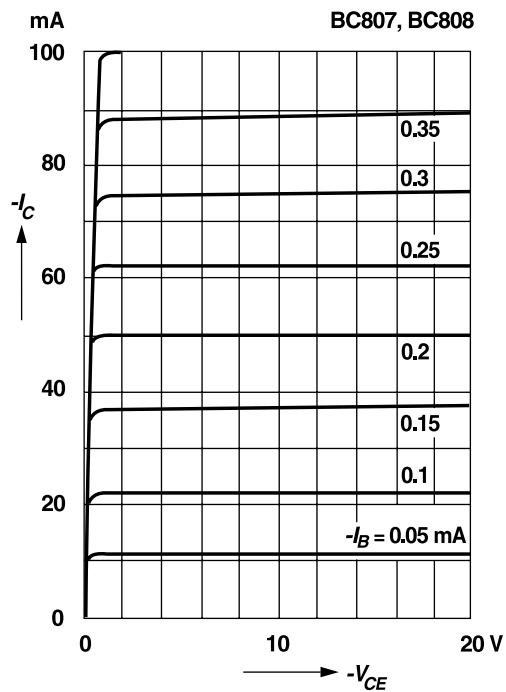


Common emitter
collector characteristics



RATINGS AND CHARACTERISTIC CURVES BC807, BC808

Common emitter
collector characteristics



Common emitter
collector characteristics

